**Preferred Device** 

# Small Signal MOSFET 150 mAmps, 60 Volts

# N-Channel TO-92

#### **Features**

• Pb-Free Packages are Available\*

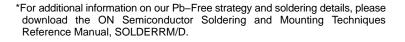
#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain – Source Voltage	$V_{DSS}$	60	Vdc
Drain–Gate Voltage ( $R_{GS} = 1.0 \text{ M}\Omega$ )	$V_{DGR}$	60	Vdc
Gate–Source Voltage – Continuous – Non–repetitive ( $t_p \le 50 \mu s$ )	V <sub>GS</sub> V <sub>GSM</sub>	±20 ±40	Vdc Vpk
Drain Current - Continuous - Pulsed	I <sub>D</sub> I <sub>DM</sub>	150 1000	mAdc
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	400 3.2	mW mW/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	312.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	T <sub>L</sub>	300	°C



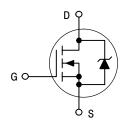


# ON Semiconductor®

http://onsemi.com

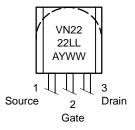
150 mA, 60 V  $R_{DS(on)}$  = 7.5  $\Omega$ 

#### N-Channel





# MARKING DIAGRAM & PIN ASSIGNMENT



A = Assembly Location Y = Year

WW = Work Week

# ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

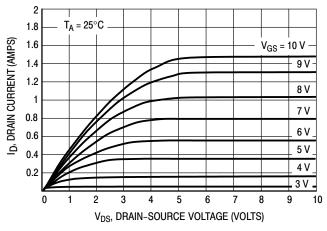
Characteristic		Symbol	Min	Max	Unit		
OFF CHARACTERISTICS							
Drain–Source Breakdown Voltage $(V_{GS} = 0, I_D = 100 \mu Adc)$		V <sub>(BR)DSS</sub>	60	-	Vdc		
Zero Gate Voltage Drain Current $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0)$ $(V_{DS} = 48 \text{ Vdc}, V_{GS} = 0, T_{J} = 125^{\circ}\text{C})$		I <sub>DSS</sub>	- -	10 500	μAdc		
Gate-Body Leakage Current, Forward (V <sub>GSF</sub> = 30 Vdc, V <sub>DS</sub> = 0)				I <sub>GSSF</sub>	-	-100	nAdc
ON CHARACTERISTICS (Note 1)							
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$		V <sub>GS(th)</sub>	0.6	2.5	Vdc		
Static Drain–Source On–Resistance ( $V_{GS}$ = 10 Vdc, $I_{D}$ = 0.5 Adc) ( $V_{GS}$ = 10 Vdc, $I_{D}$ = 0.5 Vdc, $T_{C}$ = 125°C)		r <sub>DS(on)</sub>	- -	7.5 13.5	Ω		
$\begin{aligned} &\text{Drain-Source On-Voltage} \\ &(\text{V}_{\text{GS}} = 5.0 \text{ Vdc}, \text{I}_{\text{D}} = 200 \text{ mAdc}) \\ &(\text{V}_{\text{GS}} = 10 \text{ Vdc}, \text{I}_{\text{D}} = 500 \text{ mAdc}) \end{aligned}$		V <sub>DS(on)</sub>	- -	1.5 3.75	Vdc		
On–State Drain Current $(V_{GS} = 10 \text{ Vdc}, V_{DS} \ge 2.0 \text{ V}_{DS(on)})$		I <sub>D(on)</sub>	750	-	mA		
Forward Transconductance (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 500 mAdc)		9 <sub>fs</sub>	100	-	μmhos		
DYNAMIC CHARACTERISTICS							
Input Capacitance		C <sub>iss</sub>	-	60	pF		
Output Capacitance	$(V_{DS} = 25 \text{ Vdc}, V_{GS} = 0,$ f = 1.0 MHz)	C <sub>oss</sub>	-	25			
Reverse Transfer Capacitance		C <sub>rss</sub>	-	5.0			
SWITCHING CHARACTERISTICS (Note 1)							
Turn-On Delay Time	$(V_{DD} = 15 \text{ Vdc}, I_D = 600 \text{ mA},$	t <sub>on</sub>	-	10	ns		
Turn-Off Delay Time	$R_{gen} = 25 \Omega, R_L = 23 \Omega$	t <sub>off</sub>	_	10			

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
VN2222LL	TO-92	1000 Unit / Box
VN2222LLG	TO-92 (Pb-Free)	1000 Unit / Box
VN2222LLRL	TO-92	1000 Unit / Box
VN2222LLRLRA	TO-92	2000 Tape & Reel
VN2222LLRLRAG	TO-92 (Pb-Free)	2000 Tape & Reel
VN2222LLRLRM	TO-92	2000 Unit / Ammo Box

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



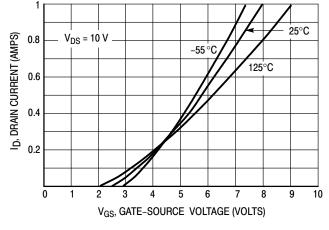
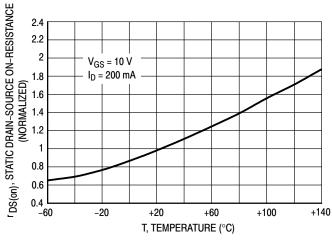


Figure 1. Ohmic Region

Figure 2. Transfer Characteristics



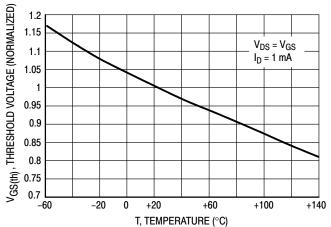
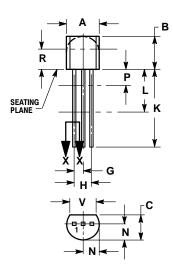


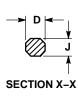
Figure 3. Temperature versus Static Drain–Source On–Resistance

Figure 4. Temperature versus Gate Threshold Voltage

#### PACKAGE DIMENSIONS

TO-92 CASE 29-11 **ISSUE AL** 





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 22:

PIN 1. SOURCE

- GATE 2.

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